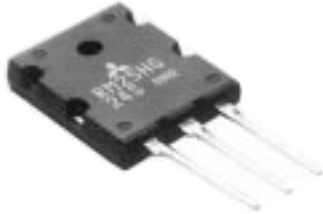


MITSUBISHI FAST RECOVERY DIODE MODULES

RM25HG-24S

HIGH SPEED SWITCHING USE
NON-INSULATED TYPE

RM25HG-24S



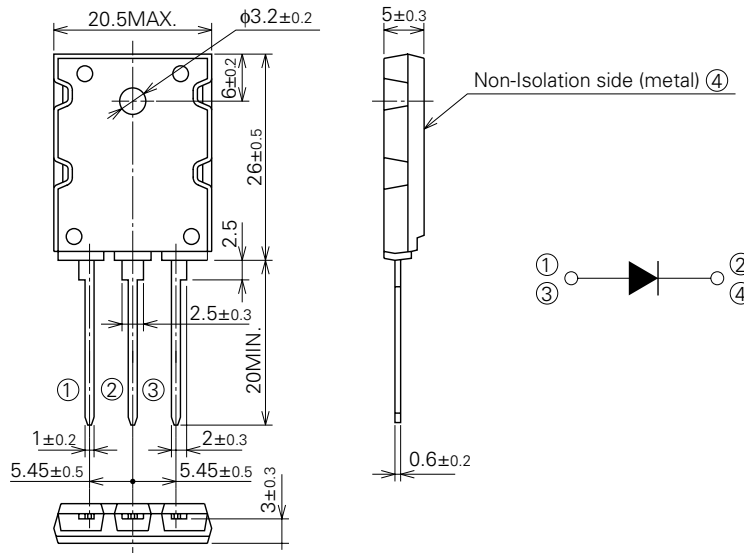
- **Idc** DC current **25A**
- **VRRM** Repetitive peak reverse voltage
..... **1200V**
- **trr** Reverse recovery time **0.3μs**
- **ONE ARM**
- **Non-Insulated Type**

APPLICATION

For snubber circuit (IPM or IGBT module)

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



RM25HG-24S

HIGH SPEED SWITCHING USE
NON-INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS (T_j=25°C)

Symbol	Parameter	Voltage class		Unit
		24		
VRRM	Repetitive peak reverse voltage	1200		V
VDRM	Non-repetitive peak reverse voltage	1350		V
VR (DC)	Reverse DC voltage	960		V

Symbol	Parameter	Conditions	Ratings	Unit
I _{DC}	DC current	Resistive load, T _c =80°C ①, ③ Collective of terminal	25	A
I _{FSM}	Surge (non-repetitive) forward current	One half cycle at 60Hz, peak value ①, ③ Collective of terminal	500	A
I ² _t	I ² _t for fusing	Value for one cycle surge current	—	A ² s
T _j	Junction temperature		-40~+150	°C
T _{stg}	Storage temperature		-40~+125	°C
—	Mounting torque	Mounting screw M3	0.59~0.98	N·m
—			6~10	kg·cm
—	Weight	Typical value	5	g

ELECTRICAL CHARACTERISTICS

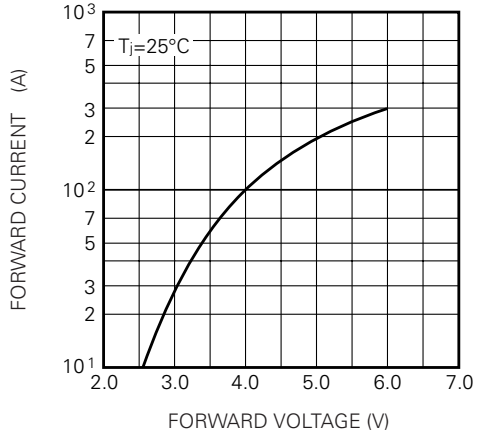
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{RRM}	Repetitive reverse current	T _j =25/125°C, VRRM applied	—	—	0.1/1.0	mA
V _{FM}	Forward voltage	T _j =25°C, I _{FM} =100A, Instantaneous meas.	—	—	4.0	V
t _{rr}	Reverse recovery time	I _{FM} =100A, T _j =25°C, di/dt=-500A/μs, V _R =600V	—	—	0.3	μs
Q _{rr}	Reverse recovery charge		—	—	—	μC
R _{th (j-c)}	Thermal resistance	Junction to case	—	—	0.5	°C/W
R _{th (c-f)}	Contact thermal resistance	Case to fin, conductive grease applied	—	—	0.5	°C/W

RM25HG-24S

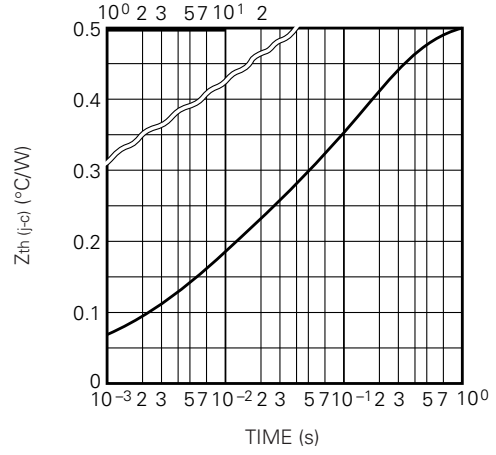
HIGH SPEED SWITCHING USE
NON-INSULATED TYPE

PERFORMANCE CURVES

MAXIMUM FORWARD CHARACTERISTIC



MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



RATED SURGE (NON-REPETITIVE) FORWARD CURRENT

